

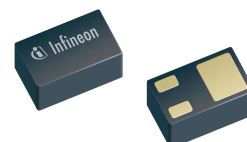
BFR843EL3

Low noise broadband pre-matched RF bipolar transistor



Product description

The BFR843EL3 is a low noise dual band pre-matched transistor in a low profile package for high speed and low power consumption applications.



Feature list

- Unique combination of high end RF performance and robustness: 20 dBm maximum RF input power and 1 kV HBM ESD hardness
- High transition frequency enables best in class noise performance at high frequencies:
 $NF_{min} = 1 \text{ dB}$ at 2.4 GHz, 1.8 V, 8 mA and 1.15 dB at 5.5 GHz, 1.8 V, 8 mA
- High gain $G_{ms} = 24 \text{ dB}$ at 2.4 GHz, 1.8 V, 15 mA and 21.5 dB at 5.5 GHz, 1.8 V, 15 mA
- $OIP_3 = 20.5 \text{ dBm}$ at 2.4 GHz, 1.8 V, 15 mA and 20.5 dBm at 5.5 GHz, 1.8 V, 15 mA
- Suitable for low voltage applications e.g. $V_{CC} = 1.2 \text{ V}$ and 1.8 V (2.85 V, 3.3 V, 3.6 V require corresponding collector resistor)

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

Potential applications

- Wireless communications: WLAN 2.4 GHz and 5-6 GHz bands, broadband LTE or WiMAX LNA
- Satellite navigation systems (e.g. GPS, GLONASS, BeiDou, Galileo...) and satellite C-band LNB (1st and 2nd stage LNA)

Device information

Table 1 Part information

Product name / Ordering code	Package	Pin configuration			Marking	Pieces / Reel
BFR843EL3 / BFR843EL3E6327XTSA1	TSLP-3-10	1 = B	2 = C	3 = E	T2	15000

Attention: ESD (Electrostatic discharge) sensitive device, observe handling precautions

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Absolute maximum ratings

1 Absolute maximum ratings

Table 2 Absolute maximum ratings at $T_A = 25\text{ °C}$ (unless otherwise specified)

Parameter	Symbol	Values		Unit	Note or test condition
		Min.	Max.		
Collector emitter voltage	V_{CEO}	–	2.25	V	Open base
			2.0		$T_A = -55\text{ °C}$, open base
Collector emitter voltage ¹⁾	V_{CES}		2.25		E-B short circuited
			2.0		$T_A = -55\text{ °C}$, E-B short circuited
Collector base voltage ²⁾	V_{CBO}		2.9		Open emitter
			2.6		$T_A = -55\text{ °C}$, open emitter
Base current	I_B	-1	5	mA	
Collector current	I_C	–	55		
RF input power	P_{RFin}		20	dBm	$f = 1.9\text{ GHz}$, matched to $50\text{ }\Omega$
ESD stress pulse	V_{ESD}	-1	1	kV	HBM, all pins, acc. to JESD22-A114
Total power dissipation ³⁾	P_{tot}	–	125	mW	$T_S \leq 103\text{ °C}$
Junction temperature	T_J		150		
Storage temperature	T_{Stg}	-55			

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Exceeding only one of these values may cause irreversible damage to the integrated circuit.

¹⁾ V_{CES} is similar to V_{CEO} due to design.

²⁾ V_{CBO} is similar to V_{CEO} due to design.

³⁾ T_S is the soldering point temperature. T_S is measured on the emitter lead at the soldering point of the PCB.

2 Thermal characteristics

Table 3 Thermal resistance

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Junction - soldering point	R_{thJS}	–	375	–	K/W	

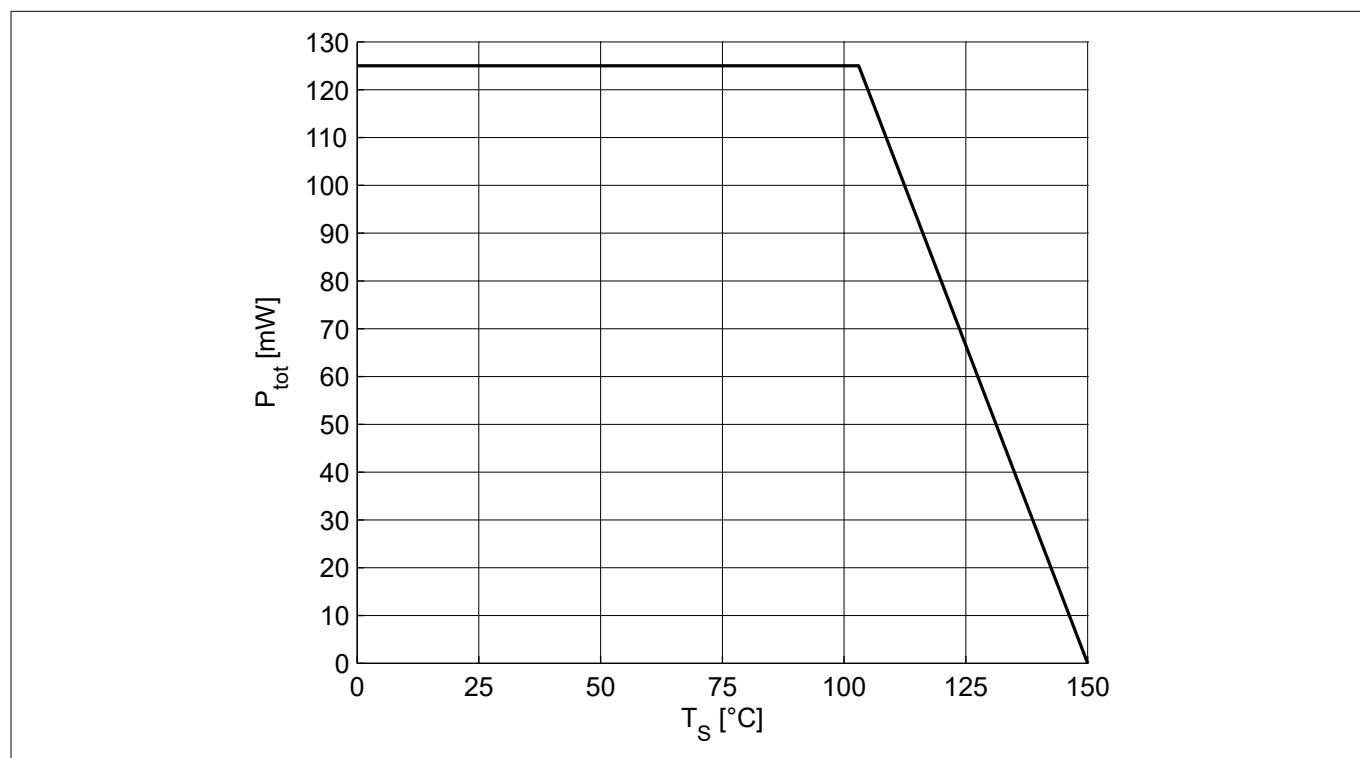


Figure 1 Total power dissipation $P_{tot} = f(T_S)$

Electrical characteristics

3 Electrical characteristics

3.1 DC characteristics

Table 4 DC characteristics at $T_A = 25\text{ °C}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	2.25	2.6	–	V	$I_C = 1\text{ mA}$, $I_B = 0$, open base
Collector emitter leakage current	I_{CES}	–	–	400 ⁴⁾	nA	$V_{CE} = 1.5\text{ V}$, $V_{BE} = 0$, E-B short circuited
Collector base leakage current	I_{CBO}			400 ⁴⁾		$V_{CB} = 1.5\text{ V}$, $I_E = 0$, open emitter
Emitter base leakage current	I_{EBO}			10 ⁴⁾	μA	$V_{EB} = 0.5\text{ V}$, $I_C = 0$, open collector
DC current gain	h_{FE}	230 –	360 260	580 –		$V_{CE} = 1.8\text{ V}$, $I_C = 1\text{ mA}$ $V_{CE} = 1.8\text{ V}$, $I_C = 15\text{ mA}$ Pulse measured

3.2 General AC characteristics

Table 5 General AC characteristics at $T_A = 25\text{ °C}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Collector base capacitance ⁵⁾	C_{CB}	–	5.26 0.07	–	pF	$f = 1\text{ MHz}$ $f = 1\text{ GHz}$ $V_{CB} = 1.8\text{ V}$, $V_{BE} = 0$, emitter grounded
Collector emitter capacitance	C_{CE}		0.42			$f = 1\text{ MHz}$, $V_{CE} = 1.8\text{ V}$, $V_{BE} = 0$, base grounded
Emitter base capacitance	C_{EB}		0.66			$f = 1\text{ MHz}$, $V_{EB} = 0.4\text{ V}$, $V_{CB} = 0$, collector grounded

⁴⁾ Maximum values not limited by the device but by the short cycle time of the 100% test.

⁵⁾ Including integrated feedback capacitance

3.3 Frequency dependent AC characteristics

Measurement setup is a test fixture with Bias-T's in a 50 Ω system, $T_A = 25^\circ\text{C}$.

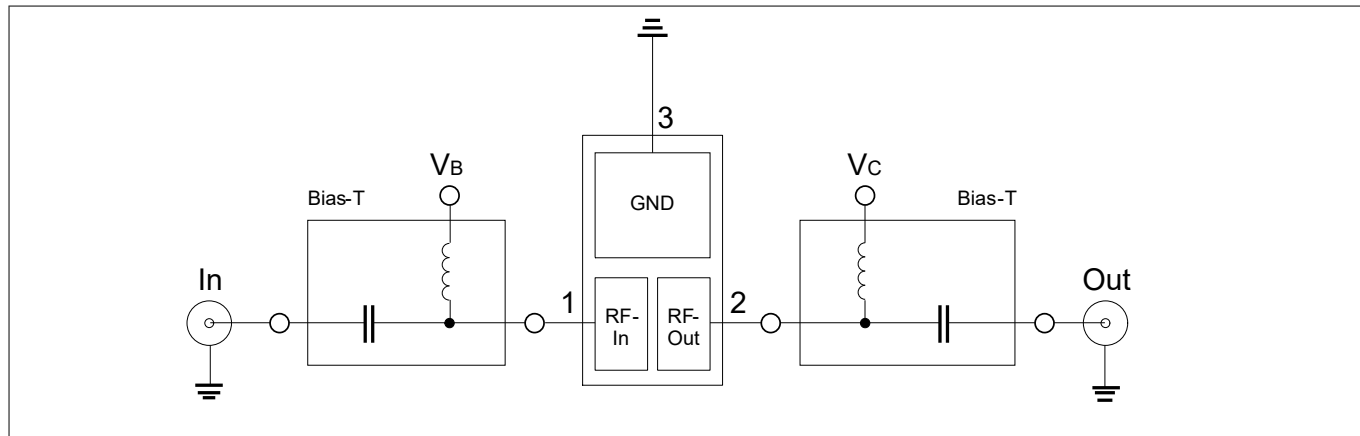


Figure 2 **Testing circuit**

Table 6 **AC characteristics, $V_{CE} = 1.8\text{ V}$, $f = 450\text{ MHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	
• Maximum power gain	G_{ms}		25.5			$I_C = 15\text{ mA}$
• Transducer gain	$ S_{21} ^2$		24.5			
Noise figure					dBm	
• Minimum noise figure	NF_{min}		0.95			$I_C = 8\text{ mA}$
• Associated gain	G_{ass}		22.5			
Linearity						
• 3rd order intercept point at output	OIP_3		23			$Z_S = Z_L = 50\ \Omega$, $I_C = 15\text{ mA}$
• 1 dB gain compression point at output	OP_{1dB}		7.5			

Electrical characteristics

Table 7 AC characteristics, $V_{CE} = 1.8 \text{ V}$, $f = 900 \text{ MHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 15 \text{ mA}$
• Maximum power gain	G_{ms}		25			
• Transducer gain	$ S_{21} ^2$		24			
Noise figure					dBm	$I_C = 8 \text{ mA}$
• Minimum noise figure	NF_{min}		0.95			
• Associated gain	G_{ass}		22			
Linearity					dBm	$Z_S = Z_L = 50 \Omega$, $I_C = 15 \text{ mA}$
• 3rd order intercept point at output	OIP_3		21.5			
• 1 dB gain compression point at output	OP_{1dB}		7			

Table 8 AC characteristics, $V_{CE} = 1.8 \text{ V}$, $f = 1.5 \text{ GHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 15 \text{ mA}$
• Maximum power gain	G_{ms}		24.5			
• Transducer gain	$ S_{21} ^2$		23			
Noise figure					dBm	$I_C = 8 \text{ mA}$
• Minimum noise figure	NF_{min}		0.95			
• Associated gain	G_{ass}		21.5			
Linearity					dBm	$Z_S = Z_L = 50 \Omega$, $I_C = 15 \text{ mA}$
• 3rd order intercept point at output	OIP_3		21.5			
• 1 dB gain compression point at output	OP_{1dB}		7			

Table 9 AC characteristics, $V_{CE} = 1.8 \text{ V}$, $f = 1.9 \text{ GHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 15 \text{ mA}$
• Maximum power gain	G_{ms}		24.5			
• Transducer gain	$ S_{21} ^2$		22.5			
Noise figure					dBm	$I_C = 8 \text{ mA}$
• Minimum noise figure	NF_{min}		1			
• Associated gain	G_{ass}		21			
Linearity					dBm	$Z_S = Z_L = 50 \Omega$, $I_C = 15 \text{ mA}$
• 3rd order intercept point at output	OIP_3		21			
• 1 dB gain compression point at output	OP_{1dB}		7			

Electrical characteristics

Table 10 AC characteristics, $V_{CE} = 1.8 \text{ V}$, $f = 2.4 \text{ GHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 15 \text{ mA}$
• Maximum power gain	G_{ms}		24			
• Transducer gain	$ S_{21} ^2$		22			
Noise figure					dB	$I_C = 8 \text{ mA}$
• Minimum noise figure	NF_{min}		1			
• Associated gain	G_{ass}		20			
Linearity					dBm	$Z_S = Z_L = 50 \Omega$, $I_C = 15 \text{ mA}$
• 3rd order intercept point at output	OIP_3		20.5			
• 1 dB gain compression point at output	OP_{1dB}		6			

Table 11 AC characteristics, $V_{CE} = 1.8 \text{ V}$, $f = 3.5 \text{ GHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 15 \text{ mA}$
• Maximum power gain	G_{ms}		23			
• Transducer gain	$ S_{21} ^2$		19.5			
Noise figure					dB	$I_C = 8 \text{ mA}$
• Minimum noise figure	NF_{min}		1.05			
• Associated gain	G_{ass}		18.5			
Linearity					dBm	$Z_S = Z_L = 50 \Omega$, $I_C = 15 \text{ mA}$
• 3rd order intercept point at output	OIP_3		20.5			
• 1 dB gain compression point at output	OP_{1dB}		6			

Table 12 AC characteristics, $V_{CE} = 1.8 \text{ V}$, $f = 5.5 \text{ GHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 15 \text{ mA}$
• Maximum power gain	G_{ms}		21.5			
• Transducer gain	$ S_{21} ^2$		16.5			
Noise figure					dB	$I_C = 8 \text{ mA}$
• Minimum noise figure	NF_{min}		1.15			
• Associated gain	G_{ass}		15.5			
Linearity					dBm	$Z_S = Z_L = 50 \Omega$, $I_C = 15 \text{ mA}$
• 3rd order intercept point at output	OIP_3		20.5			
• 1 dB gain compression point at output	OP_{1dB}		4.5			

Electrical characteristics

Table 13 AC characteristics, $V_{CE} = 1.8 \text{ V}$, $f = 10 \text{ GHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 15 \text{ mA}$
• Maximum power gain	G_{ma}		14.5			
• Transducer gain	$ S_{21} ^2$		10.5			
Noise figure					dBm	$I_C = 8 \text{ mA}$
• Minimum noise figure	NF_{min}		1.35			
• Associated gain	G_{ass}		10.5			
Linearity					dBm	$Z_S = Z_L = 50 \Omega$, $I_C = 15 \text{ mA}$
• 3rd order intercept point at output	OIP_3		17			
• 1 dB gain compression point at output	OP_{1dB}		1.5			

Note: $G_{ms} = |S_{21}| / |S_{12}|$ for $k < 1$; $G_{ma} = |S_{21}| / |S_{12}| \cdot I(k - (k^2 - 1)^{1/2})$ for $k > 1$. In order to get the NF_{min} values stated in this chapter, the test fixture losses have been subtracted from all measured results. OIP_3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is 50Ω from 0.2 MHz to 12 GHz.

3.4 Characteristic DC diagrams

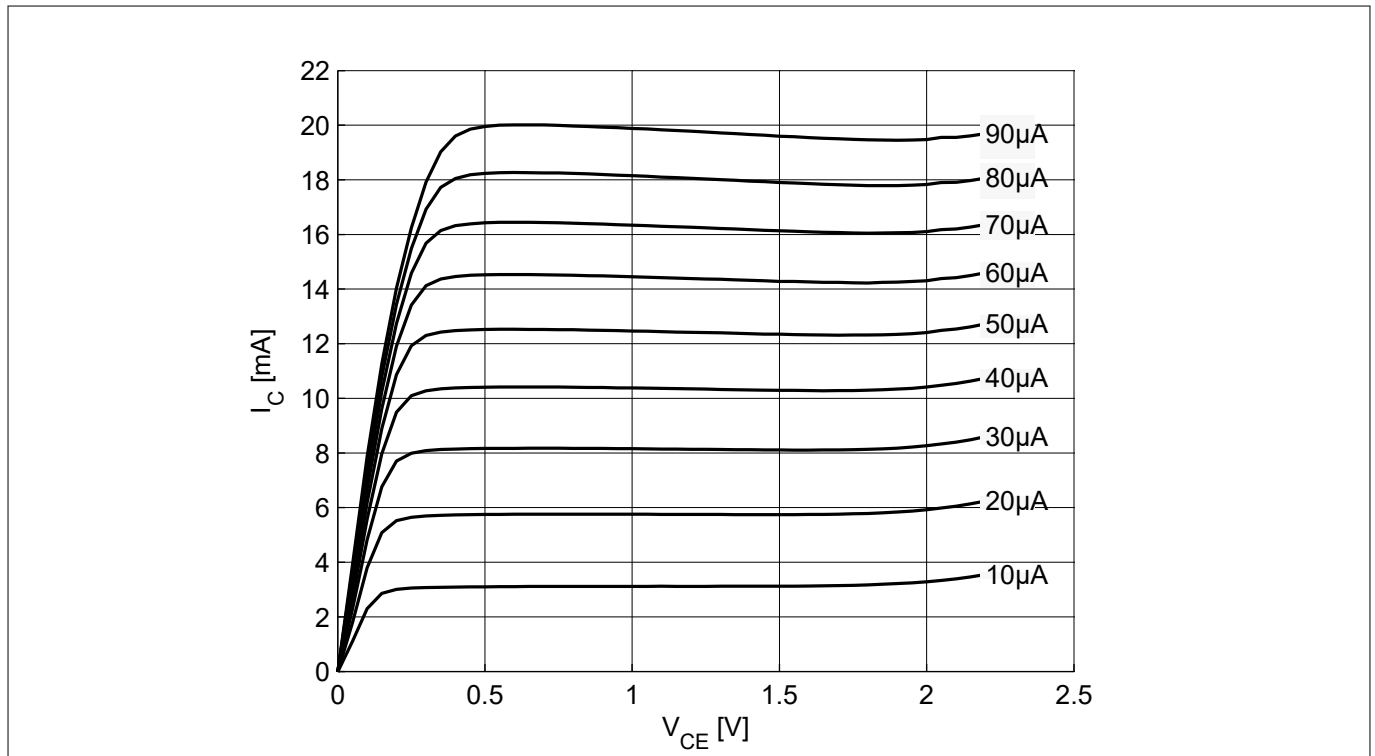


Figure 3 Collector current vs. collector emitter voltage $I_C = f(V_{CE})$, $I_B = \text{parameter}$

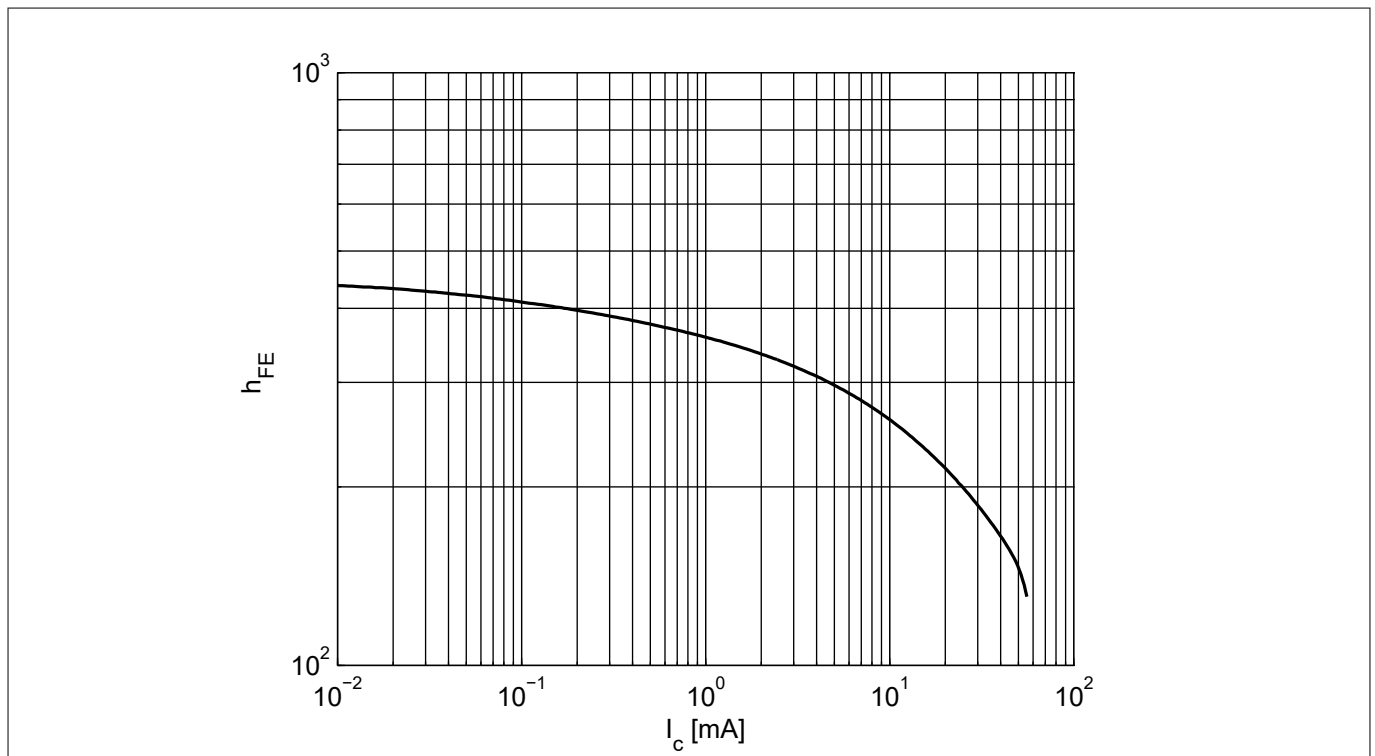


Figure 4 DC current gain $h_{FE} = f(I_C)$, $V_{CE} = 1.8 \text{ V}$

Electrical characteristics

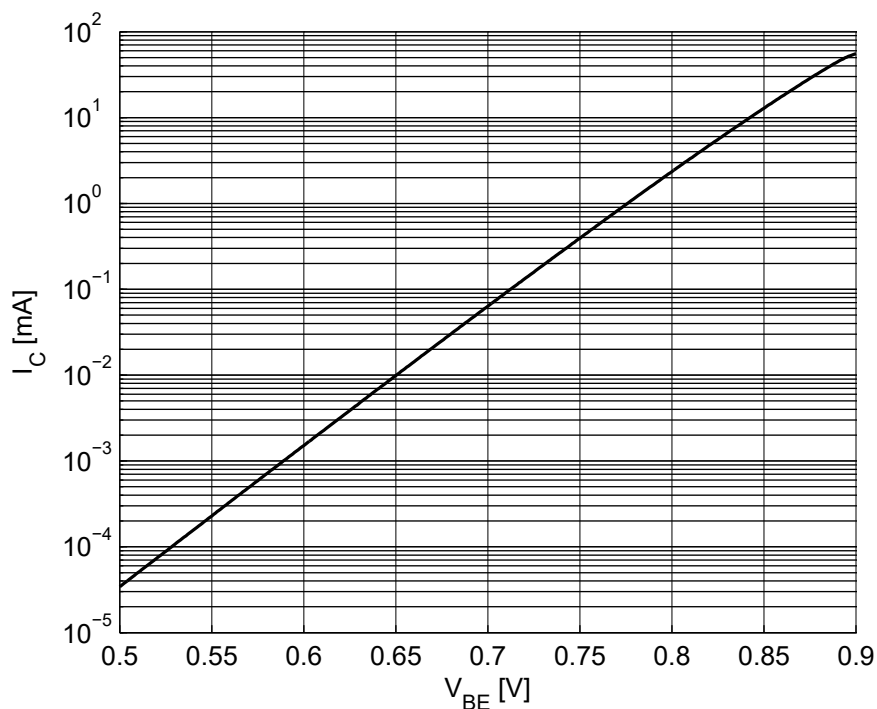


Figure 5 Collector current vs. base emitter forward voltage $I_C = f(V_{BE})$, $V_{CE} = 1.8$ V

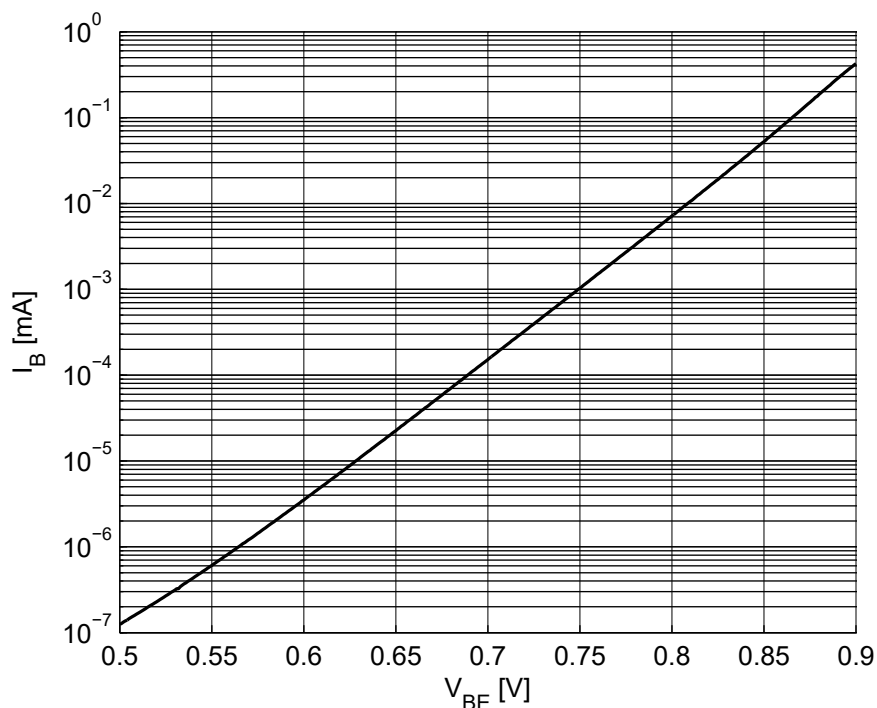
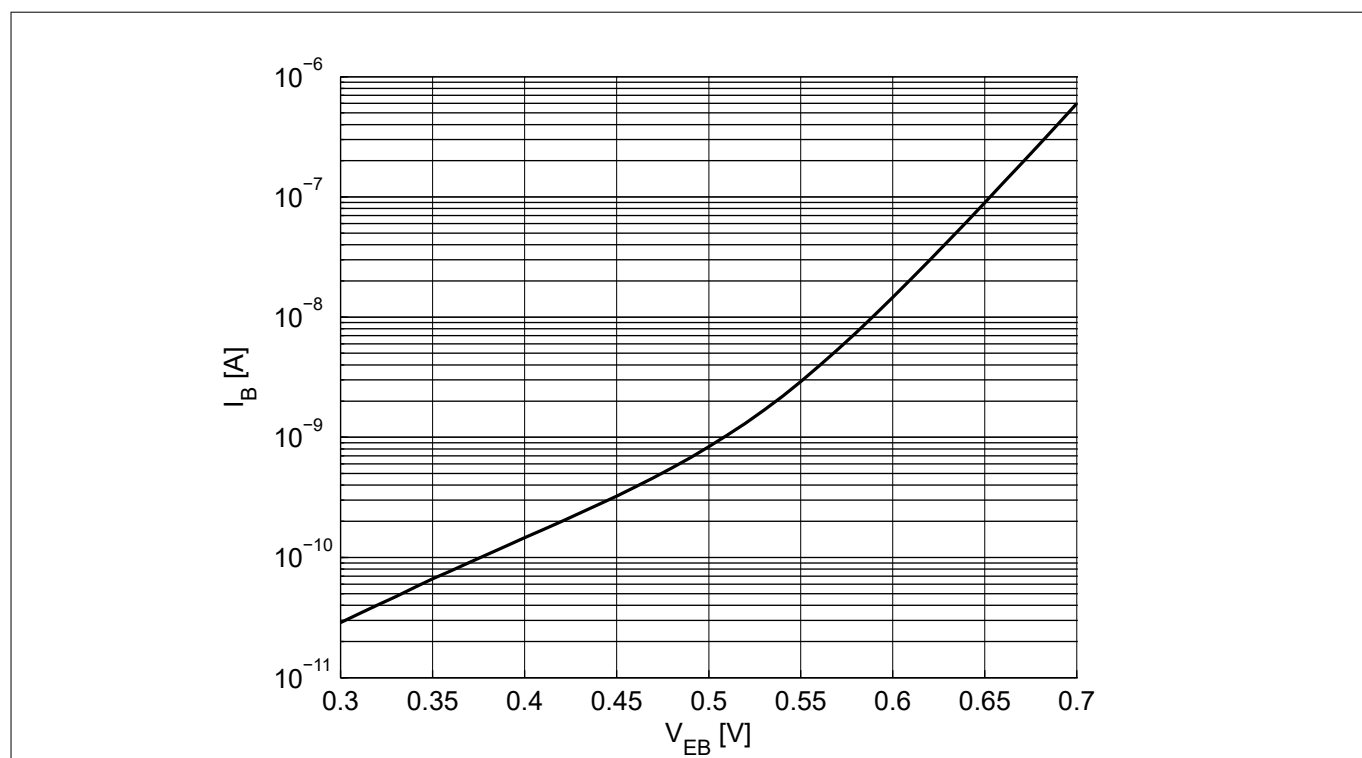


Figure 6 Base current vs. base emitter forward voltage $I_B = f(V_{BE})$, $V_{CE} = 1.8$ V

**Figure 7****Base current vs. base emitter reverse voltage $I_B = f(V_{EB})$, $V_{CE} = 1.8$ V**

3.5 Characteristic AC diagrams

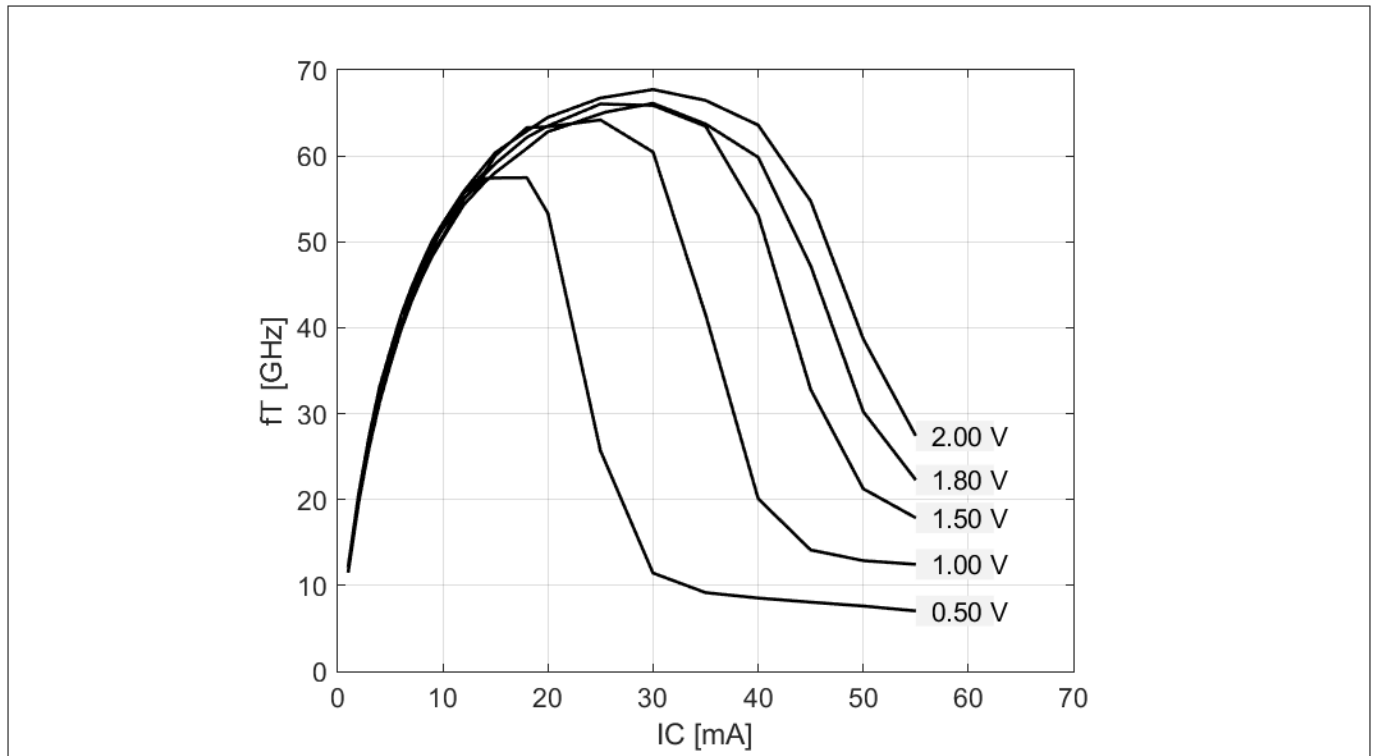


Figure 8 Transition frequency $f_T = f(I_C)$, $f = 2$ GHz, $V_{CE} = \text{parameter}$

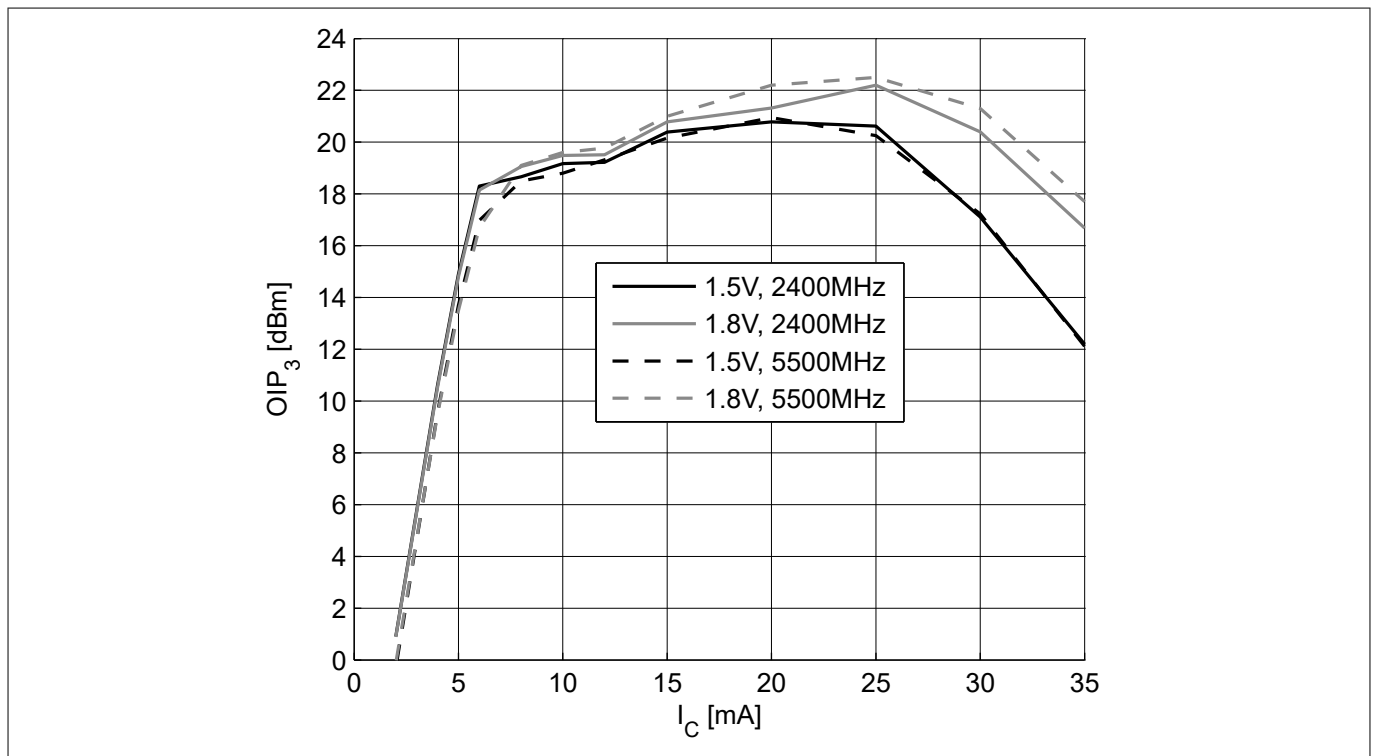


Figure 9 3rd order intercept point $OIP_3 = f(I_C)$, $Z_S = Z_L = 50 \Omega$, V_{CE} , $f = \text{parameter}$

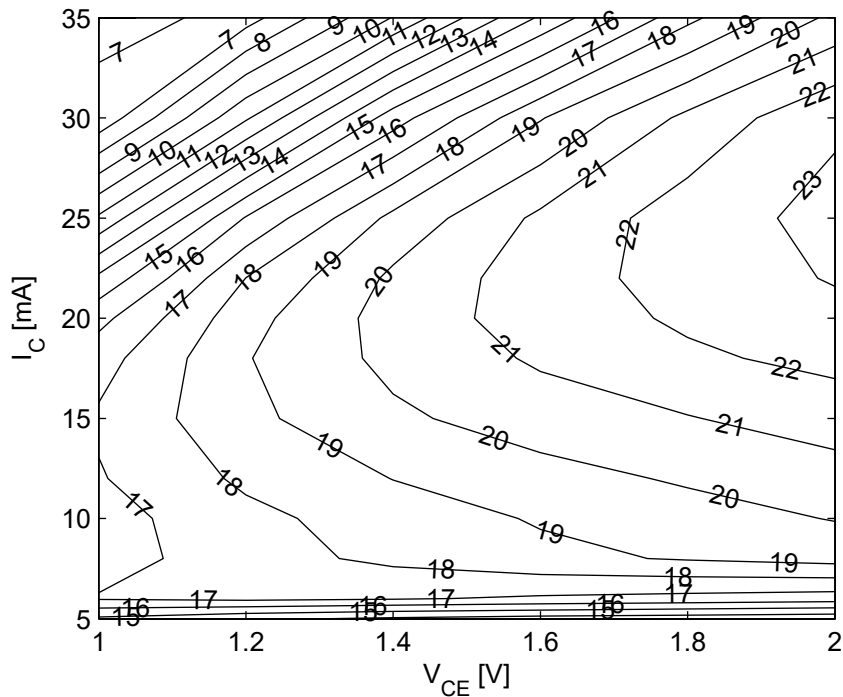


Figure 10

3rd order intercept point at output OIP_3 [dBm] = $f(I_C, V_{CE})$, $Z_S = Z_L = 50 \Omega$, $f = 5.5$ GHz

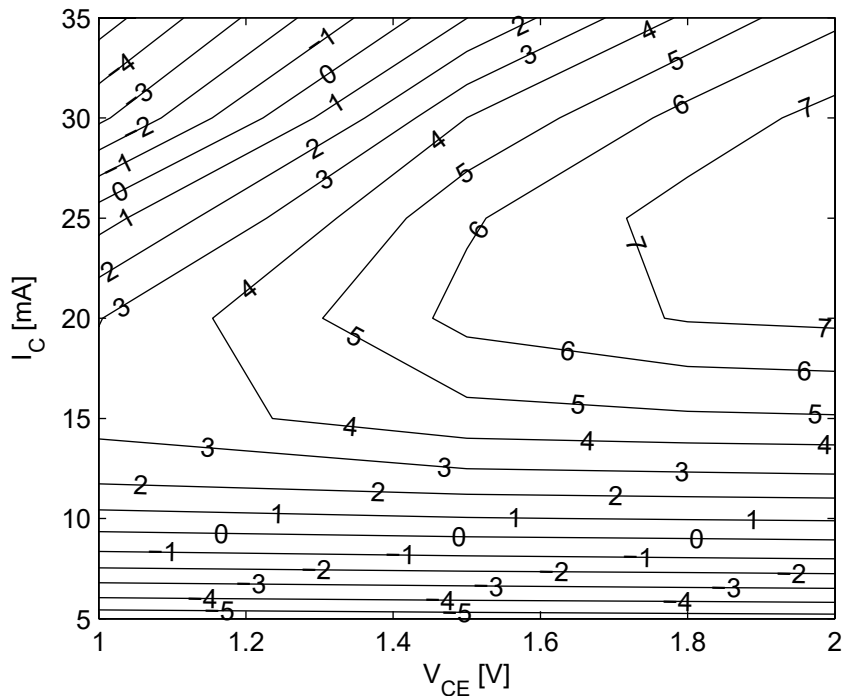


Figure 11

Compression point at output OP_{1dB} [dBm] = $f(I_C, V_{CE})$, $Z_S = Z_L = 50 \Omega$, $f = 5.5$ GHz

Electrical characteristics

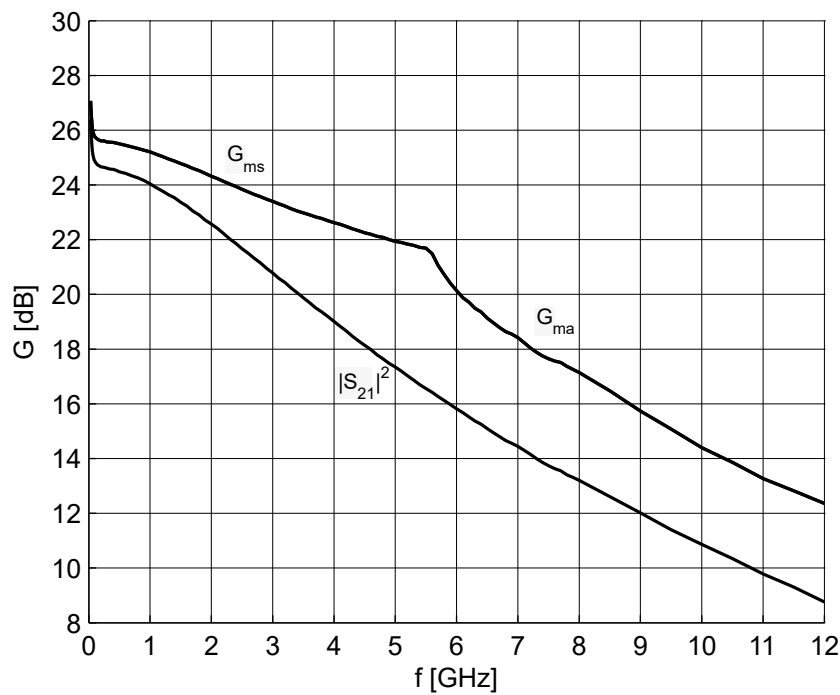


Figure 12 Gain G_{ma} , G_{ms} , $|S_{21}|^2 = f(f)$, $V_{CE} = 1.8 \text{ V}$, $I_C = 15 \text{ mA}$

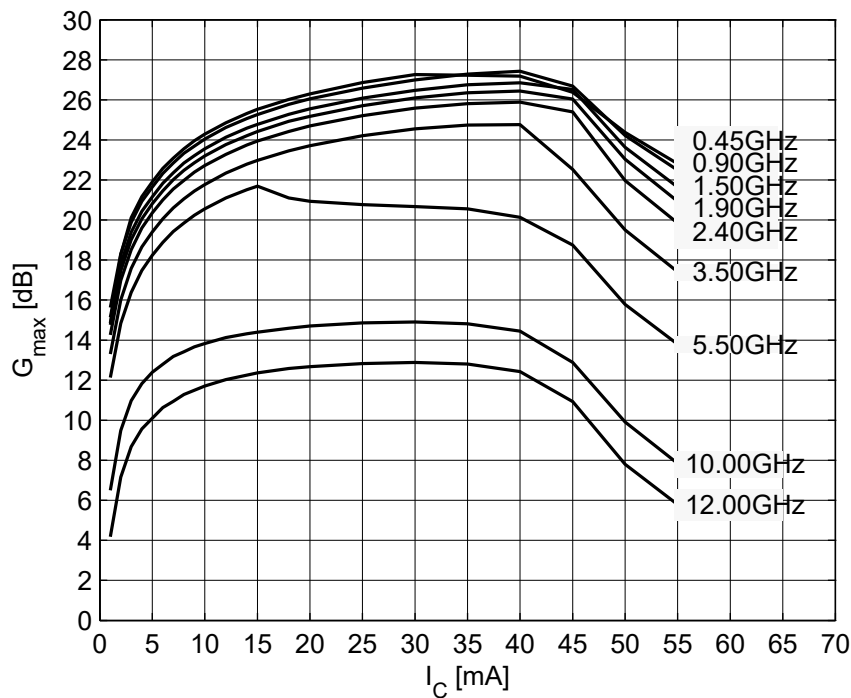


Figure 13 Maximum power gain $G_{max} = f(I_C)$, $V_{CE} = 1.8 \text{ V}$, $f = \text{parameter}$

Electrical characteristics

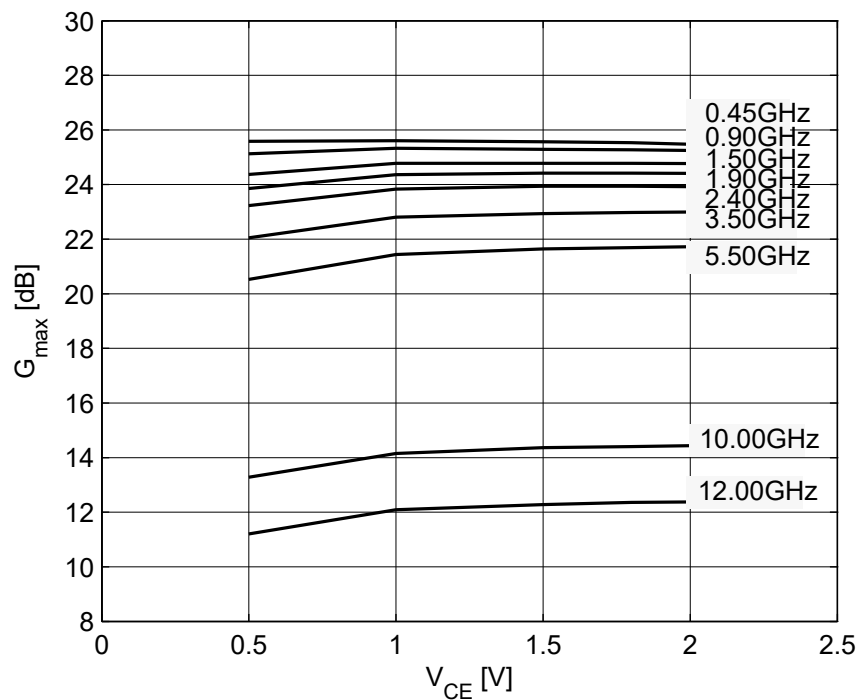


Figure 14 Maximum power gain $G_{\max} = f(V_{CE})$, $I_C = 15 \text{ mA}$, $f = \text{parameter}$

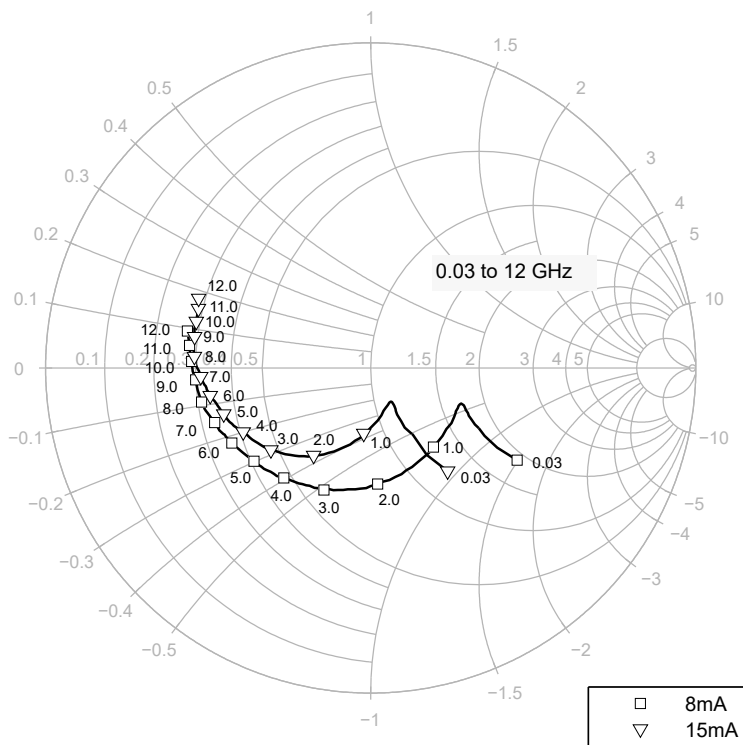


Figure 15 Input reflection coefficient $S_{11} = f(f)$, $V_{CE} = 1.8 \text{ V}$, $I_C = 8 / 15 \text{ mA}$

Electrical characteristics

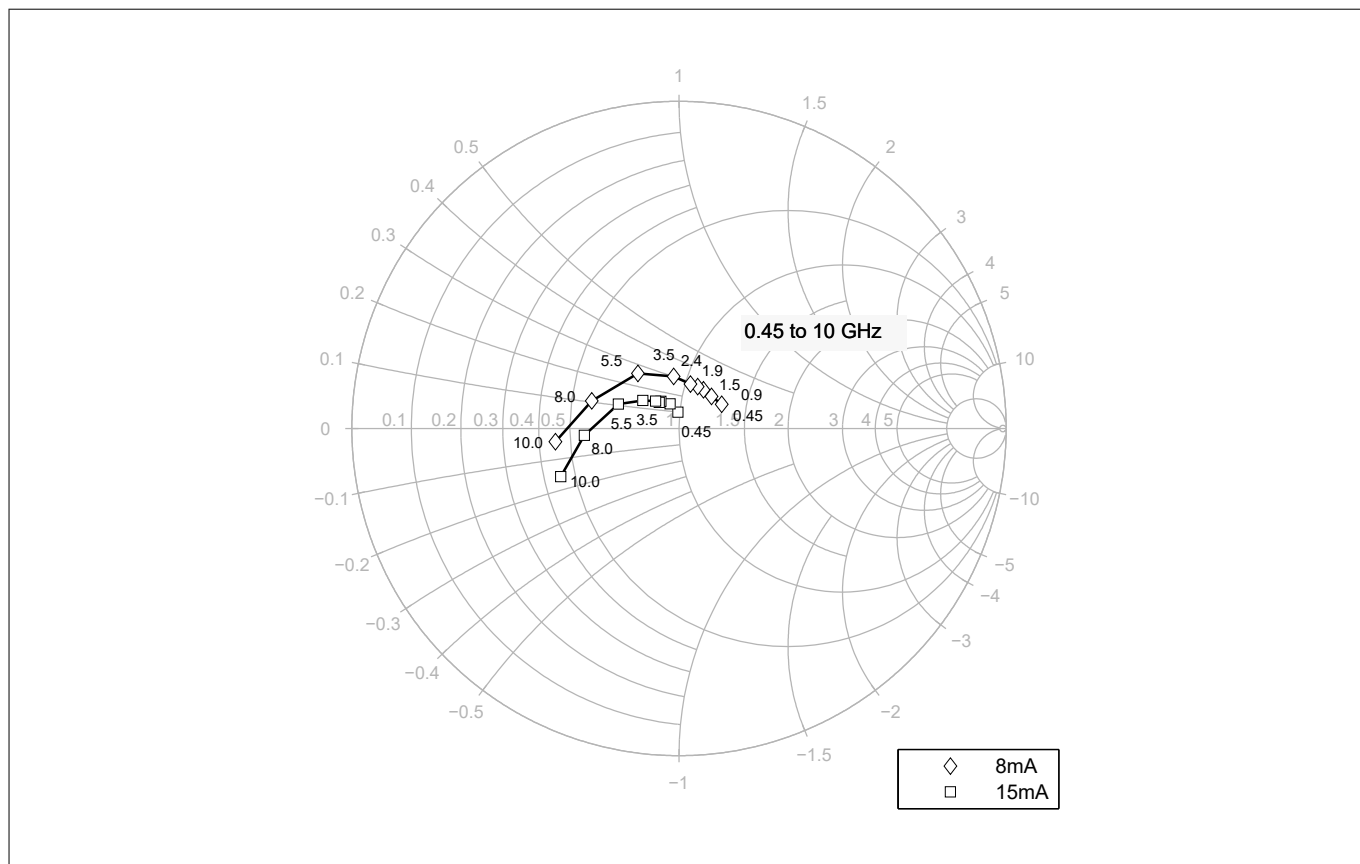


Figure 16 Source impedance for minimum noise figure $Z_{s,opt} = f(f)$, $V_{CE} = 1.8 \text{ V}$, $I_C = 8 / 15 \text{ mA}$

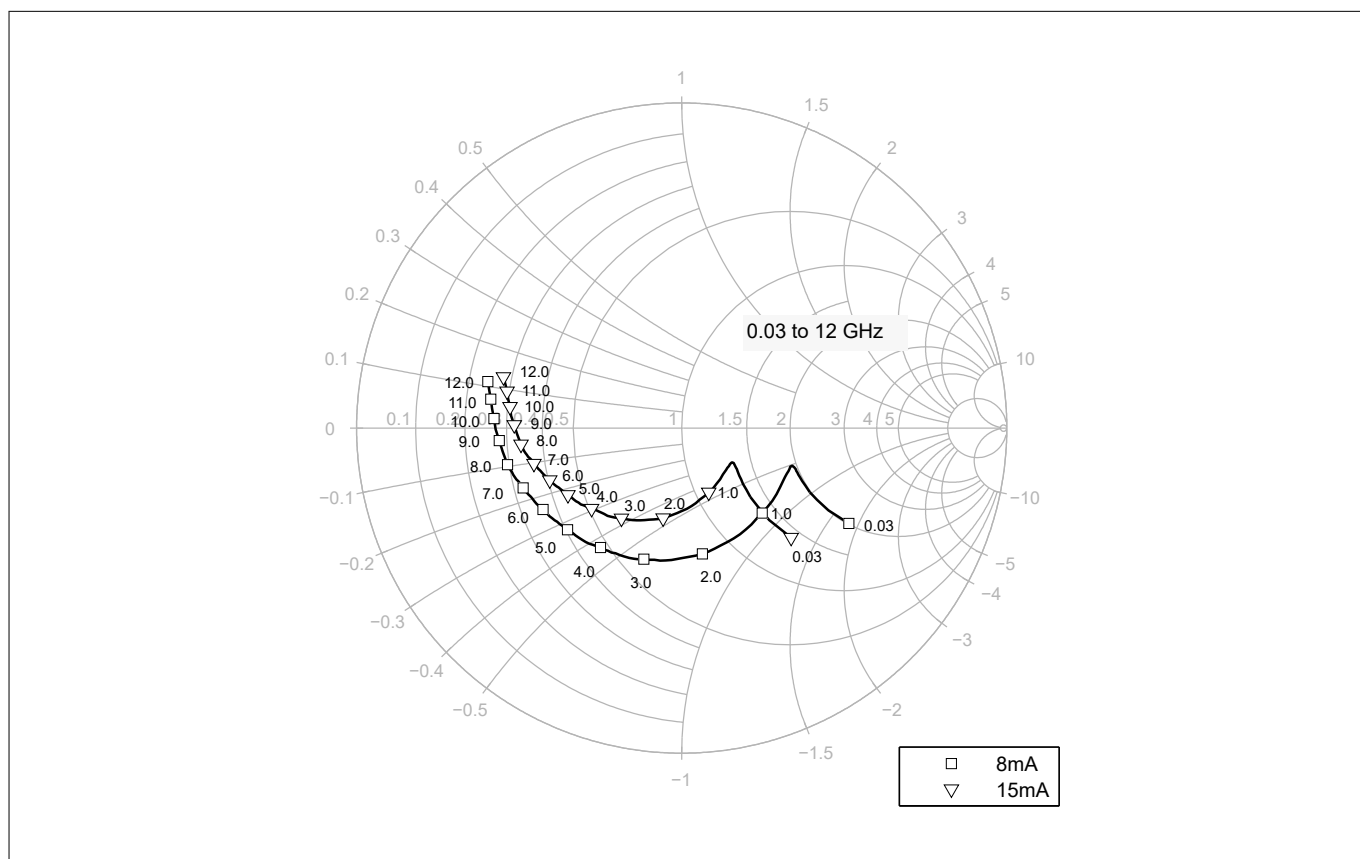


Figure 17 Output reflection coefficient $S_{22} = f(f)$, $V_{CE} = 1.8 \text{ V}$, $I_C = 8 / 15 \text{ mA}$

Electrical characteristics

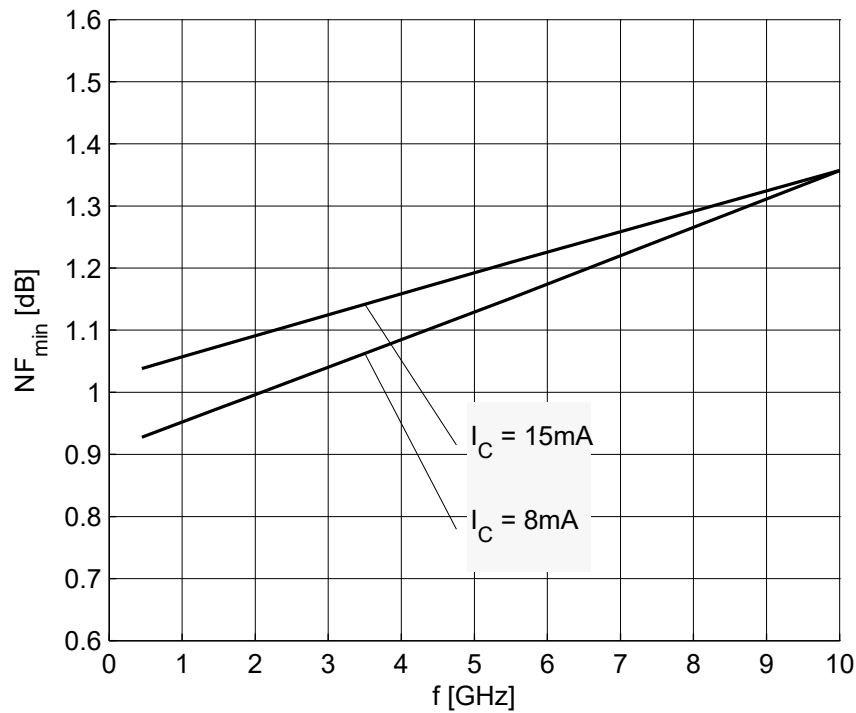


Figure 18

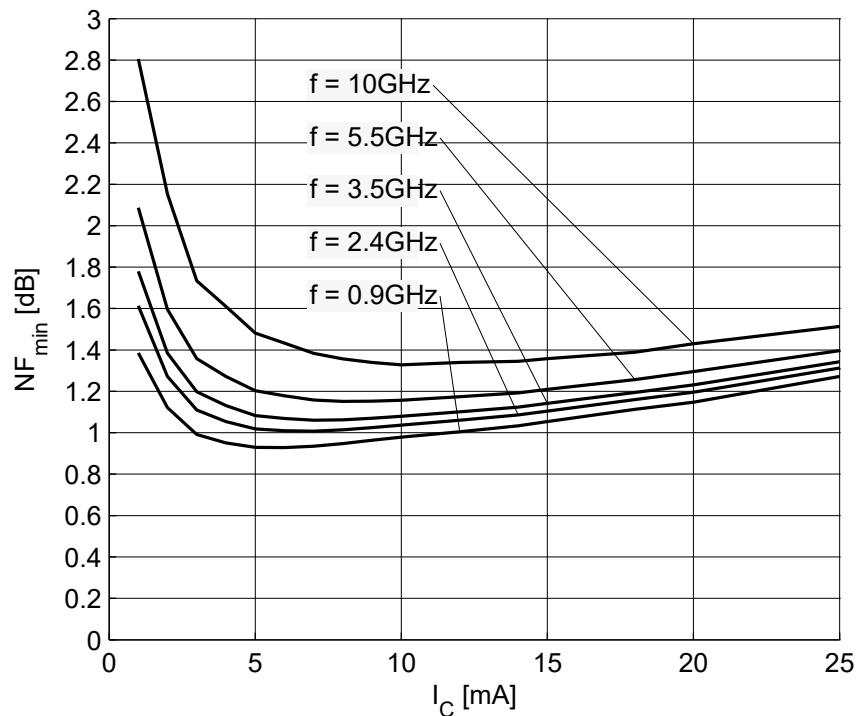
Noise figure $NF_{min} = f(f)$, $V_{CE} = 1.8\text{ V}$, $Z_S = Z_{S,opt}$, $I_C = 8 / 15\text{ mA}$ 

Figure 19

Noise figure $NF_{min} = f(I_C)$, $V_{CE} = 1.8\text{ V}$, $Z_S = Z_{S,opt}$, $f = \text{parameter}$

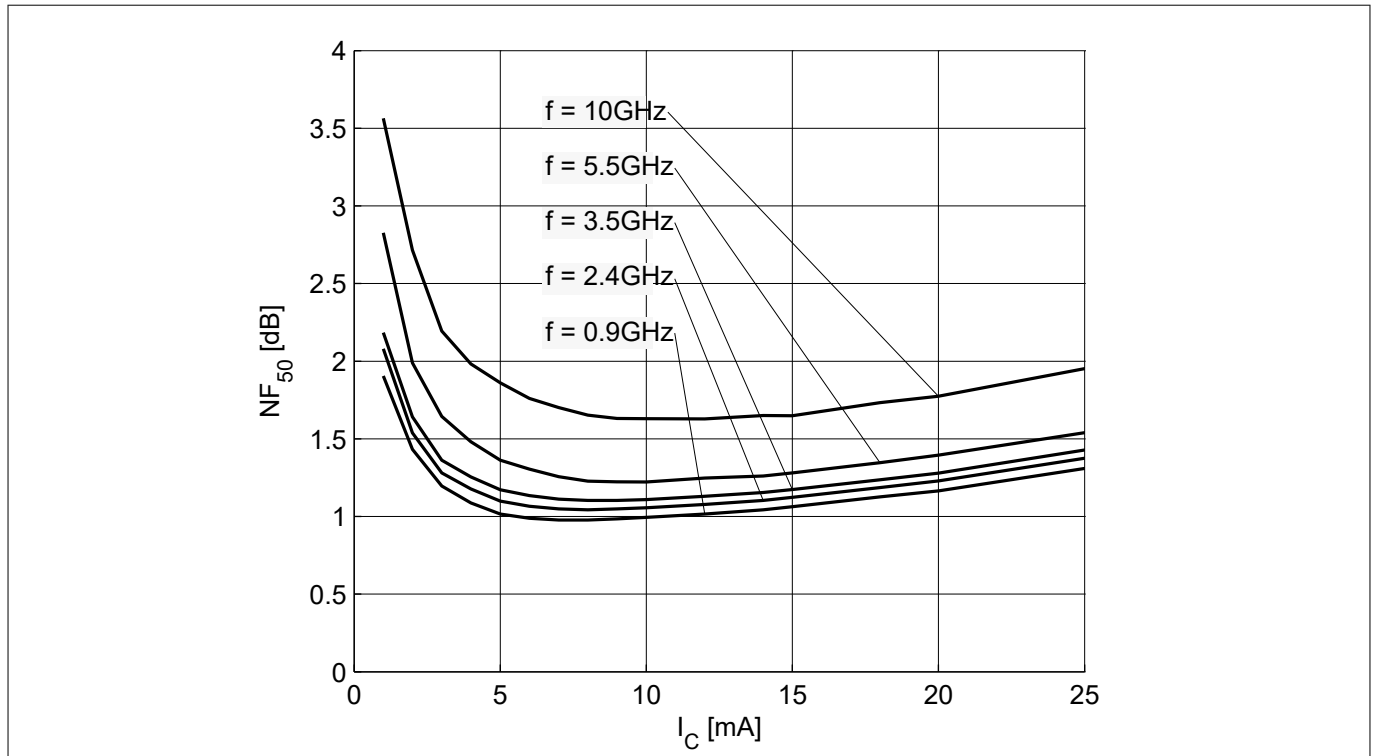


Figure 20 Noise figure $NF_{50} = f(I_C)$, $V_{CE} = 1.8\text{ V}$, $Z_S = 50\ \Omega$, $f = \text{parameter}$

Note: The curves shown in this chapter have been generated using typical devices but shall not be considered as a guarantee that all devices have identical characteristic curves. $T_A = 25\ ^\circ\text{C}$.

4 Package information TSLP-3-10

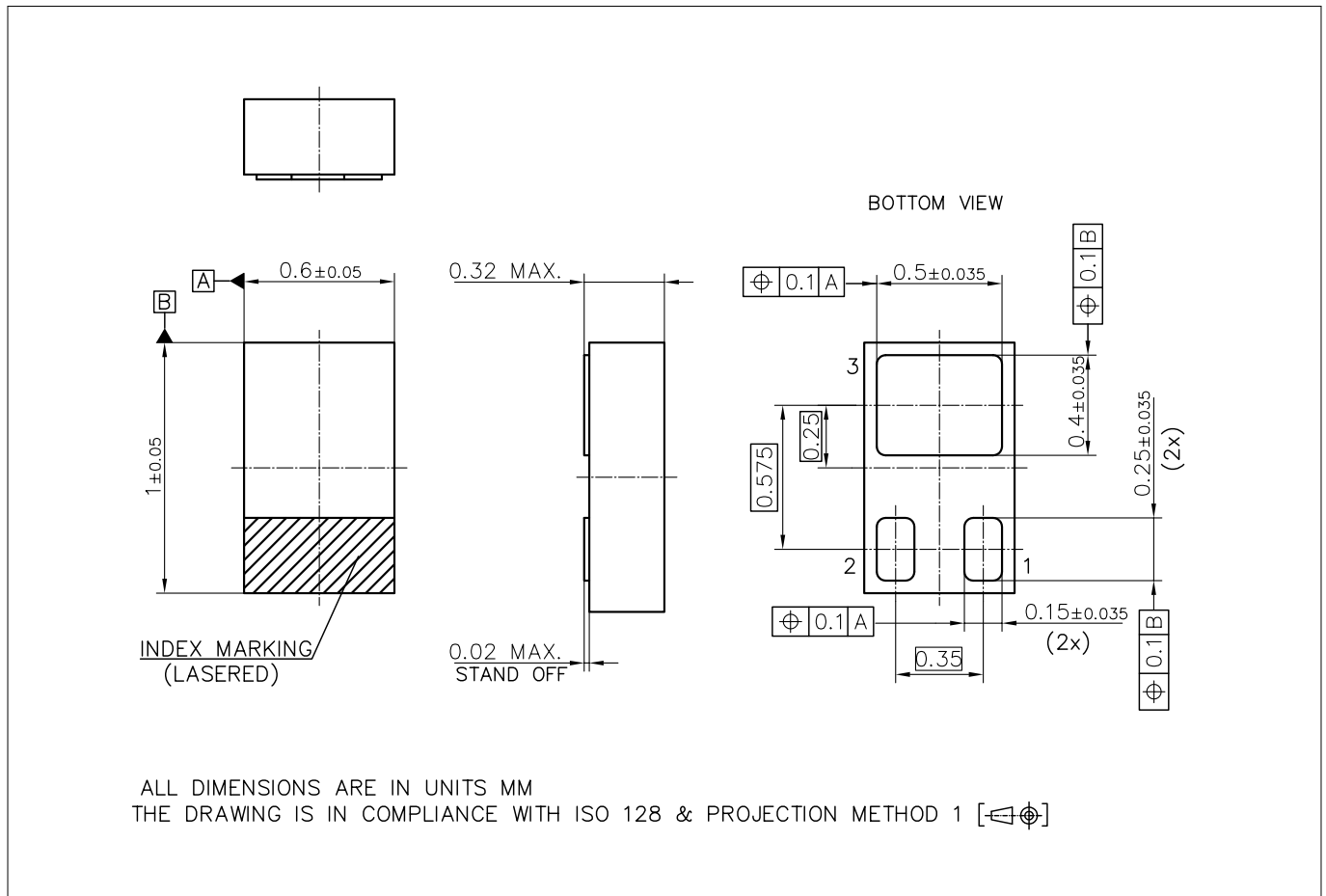


Figure 21 Package outline

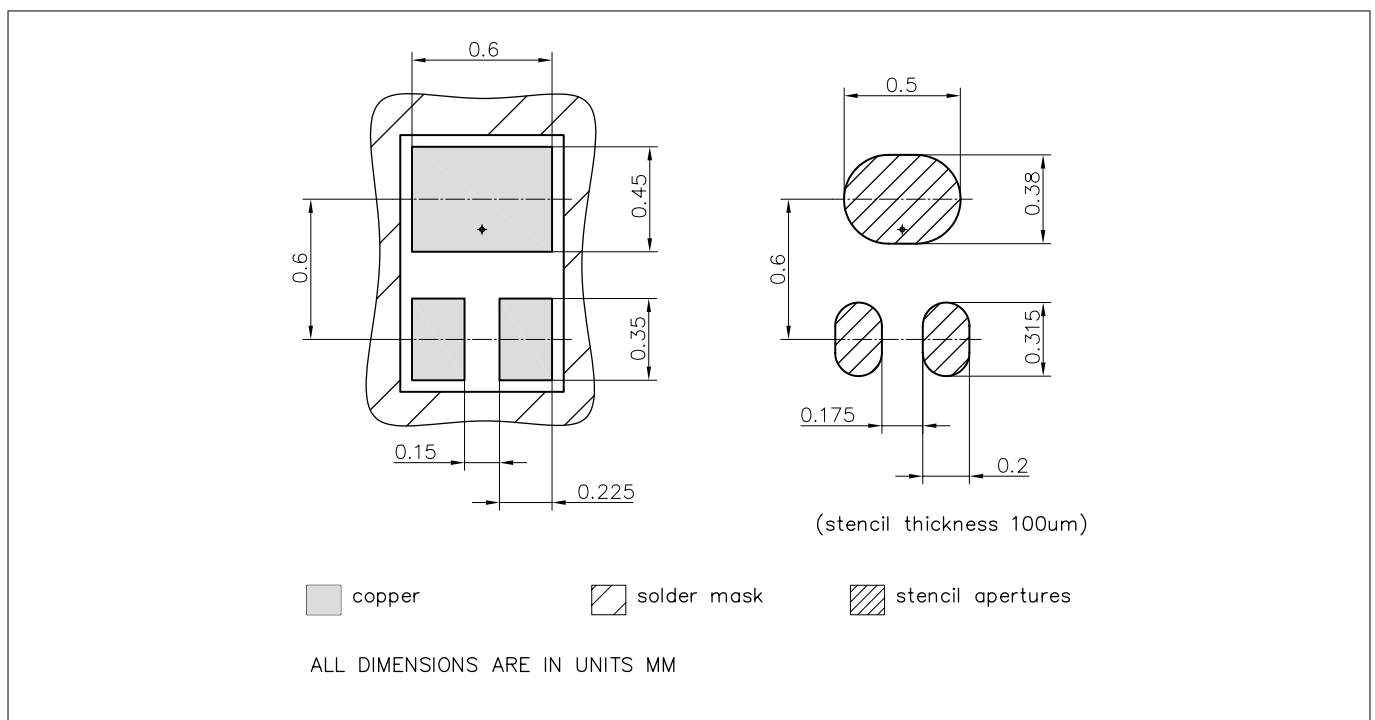


Figure 22 Foot print

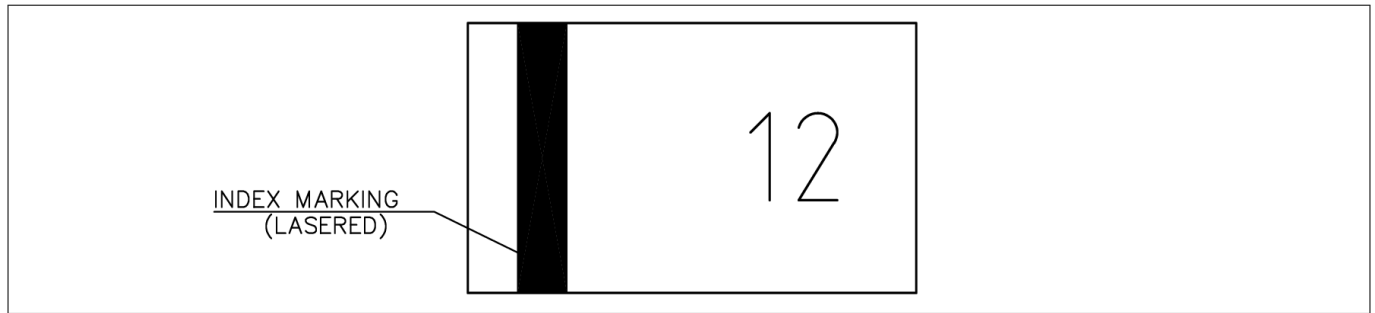


Figure 23 Marking layout example

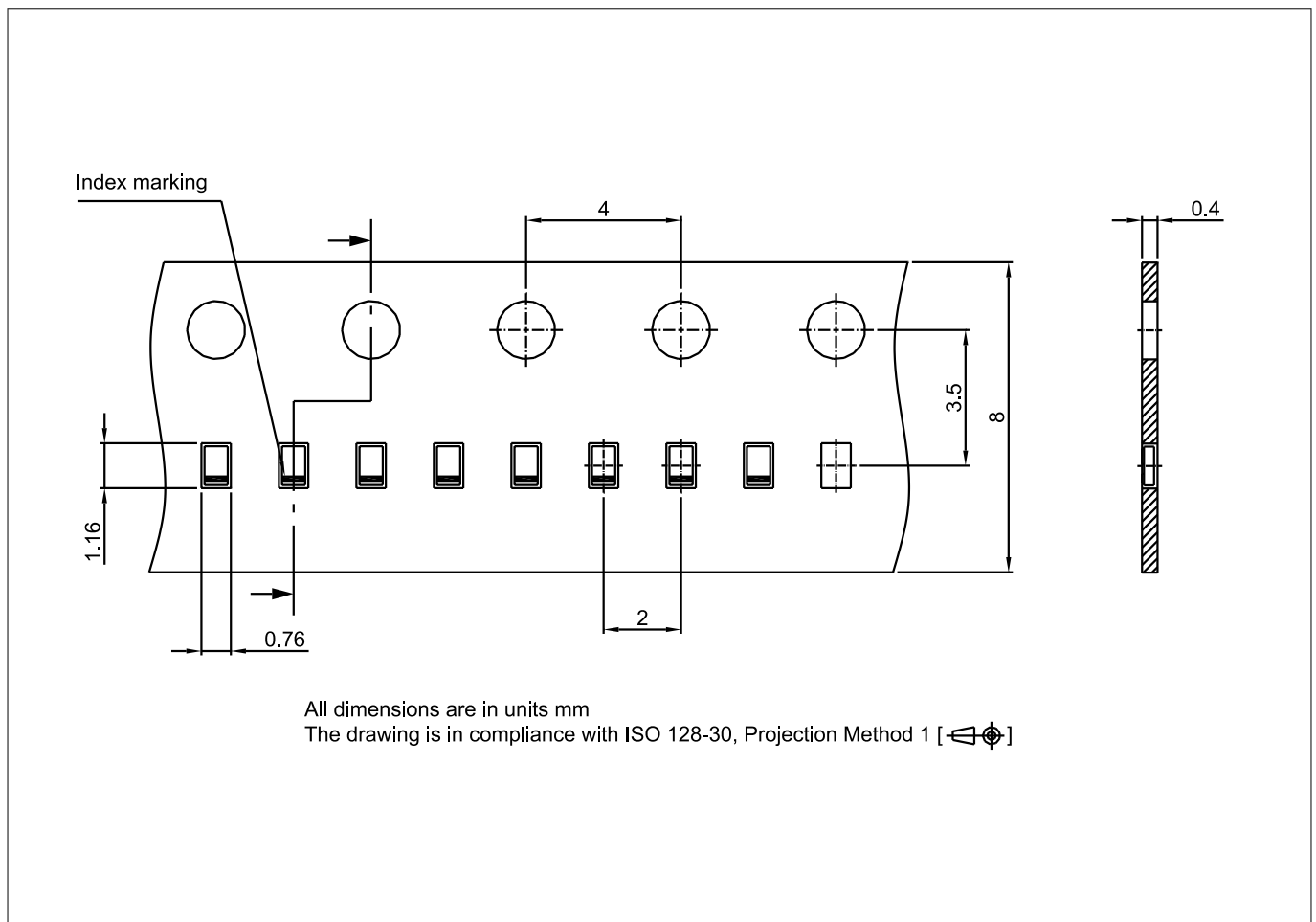


Figure 24 Tape information

Note: For recommendation on board assembly see [the website of package PG-TSLP-3-10](#).
 The marking layout is an example. For the real marking code refer to the device information on the first page. The number of characters shown in the layout example is not necessarily the real one. The marking layout can consist of less characters.

Revision history

Revision history

Document version	Date of release	Description of changes
2.0	2018-09-26	New datasheet layout
2.1	2023-12-12	- Transition frequency curve added - Tape change: New tape drawing

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Edition 2023-12-12

Published by

Infineon Technologies AG
81726 Munich, Germany

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Document reference
IFX-nea1519203763194

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